

**/ Descriptions**

TO-92          PNP          Silicon PNP transistor in a TO-92 Plastic Package.

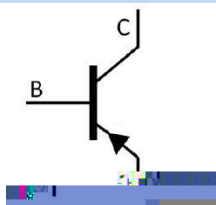
**/ Features**

High voltage. HF Product.

**/ Applications**

High voltage control circuit.

**/ Equivalent Circuit**



**/ Pinning**



PIN1 Collector          PIN 2 Base          PIN 3 Emitter

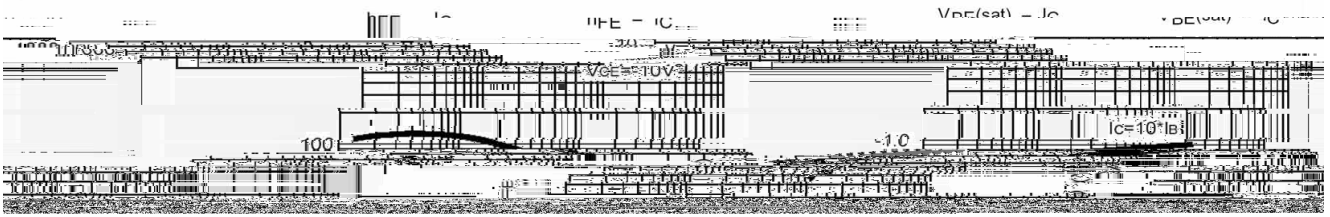
**/ hFE Classifications & Marking**

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	-400	V
Collector to Emitter Voltage	$V_{CEO}$	-400	V
Emitter to Base Voltage	$V_{EBO}$	-5.0	V
Collector Current - Continuous	$I_C$	-300	mA
Collector Power Dissipation	$P_C$	625	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=-100\mu A$ $I_E=0$	-400			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=-1.0mA$ $I_B=0$	-400			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=-100\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=-300V$ $I_E=0$			-0.1	$\mu A$
Collector Cut-Off Current	$I_{CES}$	$V_{CE}=-400V$ $V_{BE}=0$			-1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=-4.0V$ $I_C=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-10V$ $I_C=-10mA$	80		300	
	$h_{FE(2)}$	$V_{CE}=-10V$ $I_C=-1.0mA$	70			
	$h_{FE(3)}$	$V_{CE}=-10V$ $I_C=-100mA$	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-1.0mA$			-0.2	V
	$V_{CE(sat)(2)}$	$I_C=-50mA$ $I_B=-5.0mA$			-0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-10mA$ $I_B=-1.0mA$			-0.75	V
Transition Frequency	$f_T$	$V_{CE}=-5.0V$ $I_C=-10mA$ $f=30MHz$	50			MHz

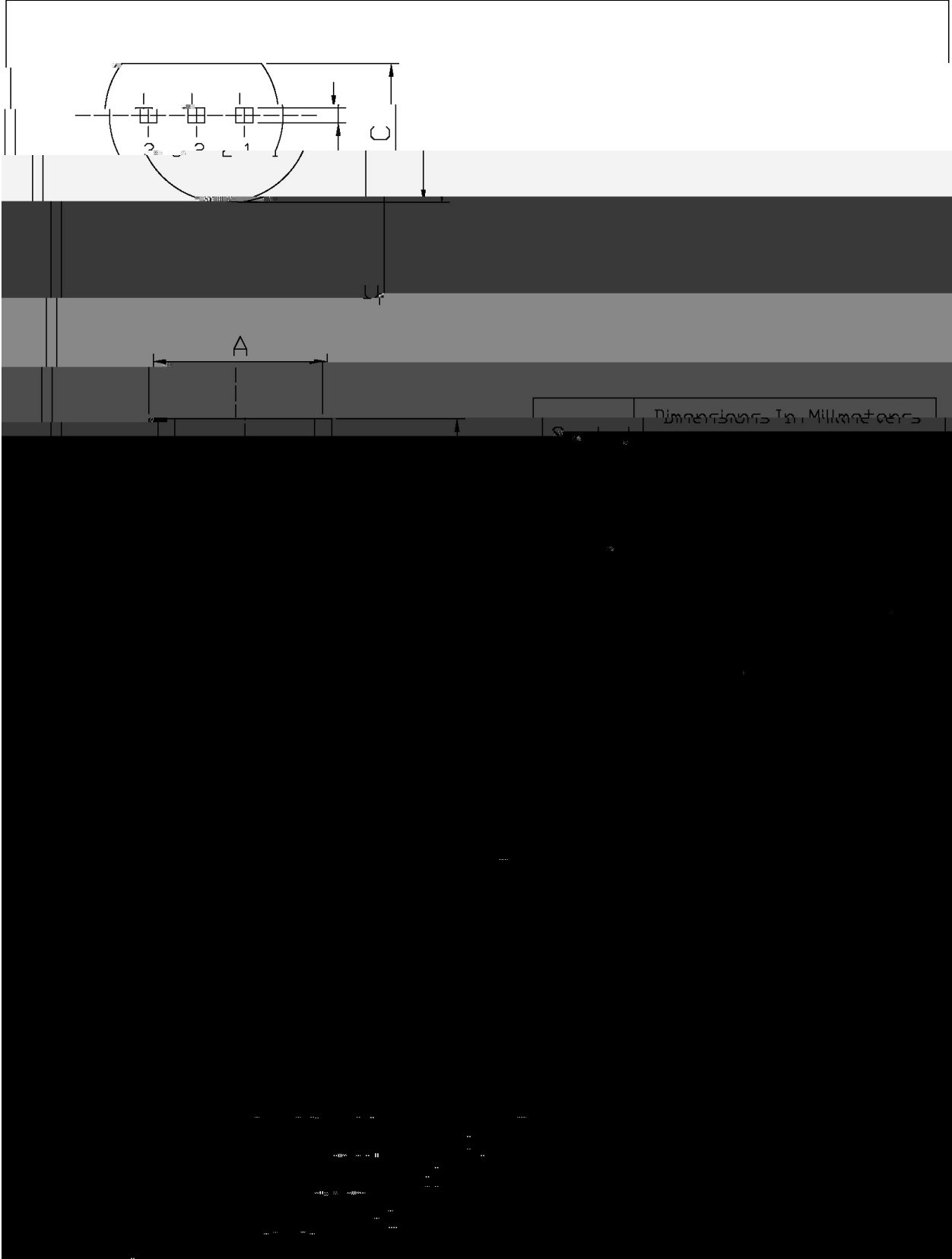
/ Electrical Characteristic Curve



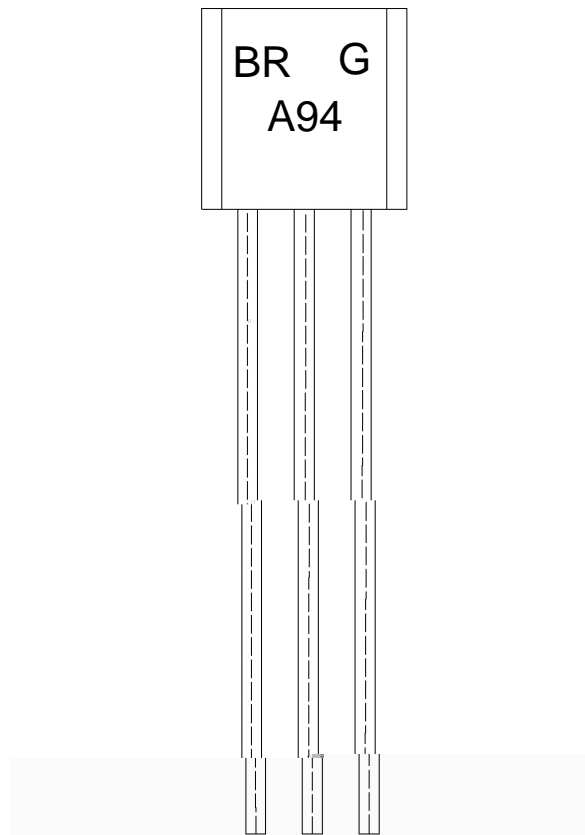
/ Package Dimensions

TO-92

Unit: mm



**/ Marking Instructions**



BR:

G:

A 94

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Note:

BR: Company Code.

G: Halogen Free Product

A94: Product Type.

\*\*\*\*: Lot No. Code,code change with Lot No.

**MPSA94G**  
Rev.F Apr.-2019